e3511 SINGLE WAFER ASHING SYSTEM

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PC / Controller Configuration



Product Specification











True downstream mw plasma process uses a heated platen with temp up to 300° for extreme low damage Photoresist removal or light etch



Process assisted with 1KW heat lamp for better uniformity/ash rate. Solid State lamp controller eliminates calibration requirement



Features: PC/HMI

IDX Flexware

- Versatile, Flexible & Configurable
- Improve Performance and Yield
- Easy User Interface
- SECS/GEM Compliant
- Field Proven Performance
- Easy-to-Use, Configurable Display







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Features: PC/HMI

- Embedded Intel® Atom PC with Slice type I/O modules attached to the PC
- Optional quad core Intel® Atom PC
- Flash drive data storage & USB Backup for recipes/data
- Easy to see 17" touchscreen
- Optional Platen overheat protection system
- Built-in watchdog timer for safe operation
- LED status of power and Digital I/O

| Silence | Continue | Pause | Operations | Log Out | Recipe | Config | Logs | Window |
|---------|--------------|-------|------------------|---------------|---------------|----------|------|--------|
| | Inputs | | Outputs | | Analo | g Inputs | | |
| System | Power | | Hó- Emplote | Slow Purge | MFC1 | 0.00 | | EXIT |
| Gasset | te Present 💽 | | Lamp Enable | Fast Purge | MFC2 | 0.00 | | |
| Cooler | Wafer 💽 | | Red Light | Han Martinet | MFC3 | 0.00 | | |
| Platen | Lift Up | | | | RF Reflective | 0.00 |) | |
| Platen | Lift Dn 💽 | | Amber Light | Platen Heater | RF Forward | 0.00 | | |
| RF Full | / RF On 💽 💽 | | Green Light | | Temperature | 0.50 | | |
| Door O | pen 💽 | | Blue Light | | Pressure | 10.00 | | |
| Door C | losed 💽 | | Light Enable | | ATM Pressur | 6.60 | | |
| Lamp F | | | Alarm Buzzer | | EOP Signal | 0.00 | | |
| Throtti | Closed | | | | Analog | Outputs | | |
| Throtti | Opened 🧕 | | Nelel Mari | | MECI | 0.0 | 2 | |
| Platen | Overtemp 💽 | | NEC2 Valve | | MFC2 | 0.0 | | |
| Lamp L | ock 🧕 | | MFG3 Valve | | MFC3 | 0.0 | | |
| Platen | OverHeat 💽 | | Open Door | | RF Power | 0.0 | | |
| Pres Lo | w ILock 💽 | | Close Door | | Lamp Level | 0.0 | | |
| Pres Hi | gh ILock 💽 | | | Poll Pate | | | | |
| Lamp S | iensor 💽 | | Praten cill | | | | | |
| Steppe | r Moving | | Isoloation Valve | CÜ | | | | |

:27:06 operator Executing the RESUME command on Group :26:57 Cassette Cassette was Removed



Features: Sub-systems

- Power supply system with DC-DC power supplies for clean power
- Wafer cooling station with touch wafer sensor, works with substrates, glass etc.
- Advanced Hine Hatm-5 pick and place robot
- Gerling GL139 1.2kw microwave generator
- Mititoyo 3 stub mw tuning
- 6 pole mw applicator
- Automatic photoemission end-point detection



Process

| Gas Flows | O2=1000 - 4000 sccm. N2/H2 = 100-1000 sccm; N2 - 100 - 500 scc | | | | |
|--------------------------|---|-------------|--|--|--|
| Pressure | 0.5-> 5.0 torr | | | | |
| Platen Temperature | 100° – 300° C | | | | |
| µ-wave Power | 0-1200 watt at 2.45 GHz | | | | |
| Lamp Utilization | 0-100% (1000 watts) | | | | |
| Throughput | 1.2 µm blanket softbaked resist ashed to end point except for deccums \leq 300Å | | | | |
| | Descum/S.T. | 45 - 60 WPH | | | |
| | Baked Photoresist | 45 - 60 WPH | | | |
| | Implanted & Damaged Photoresist | 25 - 55 WPH | | | |
| Uniformity | Sigma, ashed to 50% of \geq 1.2 µm | | | | |
| | With in Wafer | 2% - 5% | | | |
| | Wafer to Wafer | 2% - 4% | | | |
| Ash Rate | < 200Å - ≥3.5. µm./min. | | | | |
| System Matching | 2% - 5% (I sigma) | | | | |
| Mobile Ion Concentration | IEI0/cm2 – IEII/cm2 | | | | |
| CV Shift | ≤0.1 volt | | | | |
| Particle | <0.02/cm2, size of 0.2 µm | | | | |

Reliability

MTBF $\geq 168 \text{ hr.}$ MTBA $\geq 36 \text{ hr.}$ MTTR $\leq 3 \text{ hr. for 80\% of all downs}$ MTTA<5 min.UPTIME (SEMI EI0-92 STD)89 - 95%

General Information

Substrate size4 – 8 inch 100-200 mmFootprint30" 762 mm) W x 38" (965mm) D x 58" (1473mm) HElectrical200-240 VAC. 2 Phase, 50/60 Hz, WYE configuration, 30A BreakerTypical Process GasesO2, N2/H2, N2 – regulated 18 – 23 PSIG

e3510 upgrade kit

Available as PLUG AND PLAY UPGRADE TO ANY GASONICS L3500 SERIES TOOL

Note – Due to the complexity of customer's process variations and requirements, the above process performance can deviate or be improved. Therefore, customers should submit demo samples to the Application's Lab via their sales person to establish the optimum applicable specifications and conditions. Actual numbers on reliability will depend upon specific support available through contracts, knowledge of people performing PM and sufficient consumables and spare parts on site.

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